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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

. In re United States Patent Application of:

Docket No.: 4241-685

Applicants: XU, Xueping, et al.

Conf. No.: 1430

Application No.: 10/712,351

Art Unit: 1775

Date Filed: November 13, 2003

Examiner: Timothy M. Speer

Title: LARGE AREA, UNIFORMLY LOW DISLOCATION DENSITY GAN SUBSTRATE AND PROCESS FOR MAKING THE SAME

Customer No.:

23448

**DECLARATION OF DR. ROBERT P. VAUDO UNDER 37 C.F.R. § 1.132
IN SUPPORT OF TRAVERSAL OF CLAIM REJECTIONS
IN U.S. PATENT APPLICATION NO. 10/712,351**

1. My name is Robert P. Vaudo. I have a PhD. in electrical engineering from North Carolina State University and was a Post-doctoral fellow at Boston University. I have been performing research in wide bandgap semiconductors for approximately 17 years. For more than 12 of those years I have been directly involved in the research and development of wide bandgap III-V nitride substrates, and I am named as an author or co-author of numerous papers published in technical journals relating to such materials. I am currently a Senior Scientist in the Materials Department at Cree, Inc., which is a leading innovator and manufacturer of semiconductors. I am named as a co-inventor on a large number of U.S. patents, foreign patents, and pending patent applications relating to wide bandgap III-V nitride materials, including, for example, U.S. Patent Nos. 7170095, 7118813, 6972051, 6951695, 6943095, 6765240, 6596079, 6533874, 6488767,